



ABSTRACT OF THE DISCLOSURE

EPITAXIAL SUBSTRATE FOR COMPOUND SEMICONDUCTOR
LIGHT-EMITTING DEVICE, METHOD FOR PRODUCING THE SAME AND
LIGHT-EMITTING DEVICE

In order to improve light-emission efficiency without degrading protection performance of a light-emitting layer structure a three p-type layer structure composed of first to third layers is provided in contact with a light-emitting layer structure. The first layer is an n-type AlGa_N layer that serves as a protective layer, the third layer is a Ga_N : Mg layer that serves as a contact layer and the second layer is an AlGa_N : Mg layer formed between these layers as an intermediate layer. The provision of the intermediate layer enables an InGa_N layer to be thoroughly protected from heat during growth of layers above even if the n-type AlGa_N layer is made thin, whereby the Ga_N : Mg layer can be brought near the light-emitting layer structure to enhance the efficiency of hole injection into the light-emitting layer structure and thus increase the light-emission efficiency.

(Figure 1)

